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C s s S D

C s s P A

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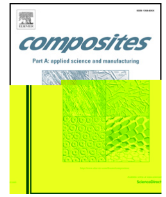

In-situ s f - s s s s ff s f f s

Ch

K C , W , L *, L H , C , L , f L , s W , K s Ess , L L , G , T P f

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A R T I C L E I N F O

Keywords:
T - s
C s s ff
S s
C s
E f s

A B S T R A C T

C , - s (3DG) f s s ss, s s s s s . H s - s - s s s (SLM) f - s (3D) s . G s *in-situ* s (CVD) s C , f 3DG s s. A f CVD SLM f s ff s s f 3DG f -s (, s ,) -s (, s f) s s ff . T 3DG/ s ff 88% 27% f (EMI) s ff s . P , s EMI s ffi- (*SE*) 47.8 B 2.7 GH *SE* f 32.3 B f 2–18 GH . T s s s s s f f s f s s s f SLM s s .

1. Introduction

G , s s f sp^2 s, s s f , s s f (2630 ^{2} $^{-1}$) [1], s (2 10^5 ^{2} V^{-1} s^{-1}) s (~5000 W $^{-1}$ K^{-1}) [2]. H , s π-π s (2D) s - s s - , s s ff s f s s s s , s , f - ss s s s s f [3]. A f f s s fi ff s s s - s. C f s s, - s - (3DG) s s s (~99.7%), s fi (~0.6 $^{-2}$) [4] s fi s f s s s , f s ss s f s f - s

(2DG), s s [5], s [6,7], s s s [4], f (EMI) s [8] s . V s s f s 3DG , f [9], [10], s f- ss [11], - [12] s . H f - s s f s s. F , f s ff f s f s [13]. S f- ss s ss (s s) s s [14]. D - s s s s f s s f s s [15]. M s s s s f f f s s , - CVD s s s s , s s s f - - [16]. B s , s s , s s f s s s

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s . T x s s (. ., s -
s), fl fi s
(. ., ss, f s) f 3DG. B s s, -
3DG s f
(. ., s , s , s f). H , s f s
s ffi
s , f s , N f
s s f
, s s 3DG s s f -
s s f s f s fi f s 17,18 .
H , s f ss s,
s f s s 3DG
s s s f s 19 .
S s (SLM), s -
f (AM) , s s f f
f s s / s x - s (3D) s
s f s , ffi
fl f *in-situ* f . T , s
s s SLM s s s f T s 20 ,
s ss s 21 , N s 22 . C s s s f /
s s f - s s s - f- - -
s s s. C N s s ,
s s s s s f
CVD s (< 0.001 . %)
ss s f- f , -
s N s s 23 . W N s
s x (> 0.1 . %) 17 , fi s
f s f ss 24 . H , -
s SLM f s s s f s f s ffi
f s f s s
fl s s
(1000–1100). F f s s s ff s
SLM s s f s 25 .
T s, f fi s s
f s - 3DG/ (3DG/C) s -
s SLM s s CVD f
. A - s - s s
s SLM f s -

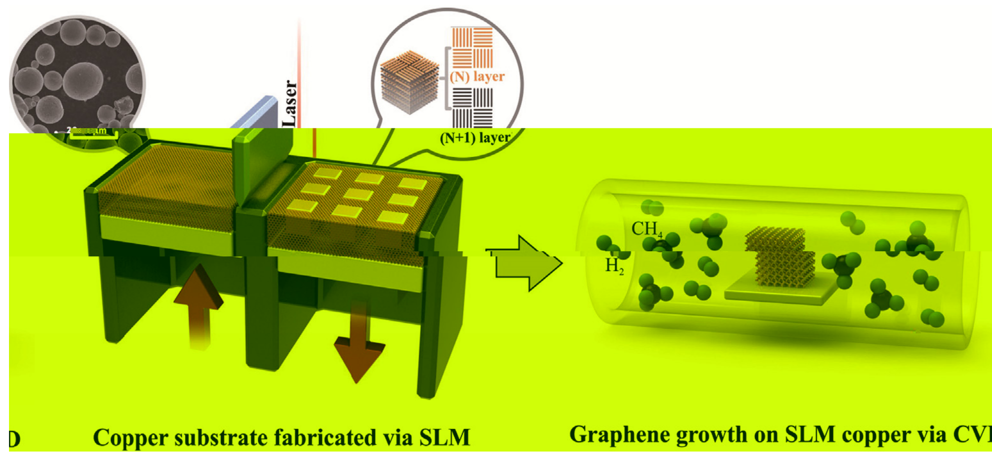

Fig. 1. Ill s f 3DG/C s s f ss: s ff l f SLM (l f) *in-situ* s ff l CVD ( ). (F f f s l s fi l , s f s f s l .)

ASTMB193-2002 s s l s f 2 2 20 3 f l l s. T l ff s s (2 10 10 3) s s (5 10 10 3) f ll ASTME1461-2013 s l s f f s s LFA (L s fl s , N s LFA457, G). R s s (SENTERRA, B , G) s s 3DG/C s ff l - l f 514 . T *S* s (*S11* *S21*) s l (VNA, A l PNA-N5244A, US) s l 2–18 GH . T l s f *SE* l, *SE* s , *SE* fl s E . 2–5 S I f .

3. Results and discussion

3.1. Formation of SLM copper

3.1.1. SLM manufacturing of copper under different line energy densities

T s ff s (l s s s) l l s s l . D ff s f s l s s ss l f s s s (F . 2) s l s l , l 30% s (A), 26.7% s l l (B), 16.7% s (C) 26.7% ss l (D). D ff s s l s , LED (J/) 27 (E . 6, l s f SI). T s l l s ss ll s f fl l f . T l ss s s ls f ffi l l ss s. I A, s s ffi l f s l s s s ffi . I B, l f s l s l s f l s s f fi . T l fl f l l s s l s ffi f f l s s l , l l s LED f 400 J/ (C). W ss LED (> 800 J/) s l , l 130 μ - s ls (D), s - s l s ss s s l f l ss s ll s l s s 28 .

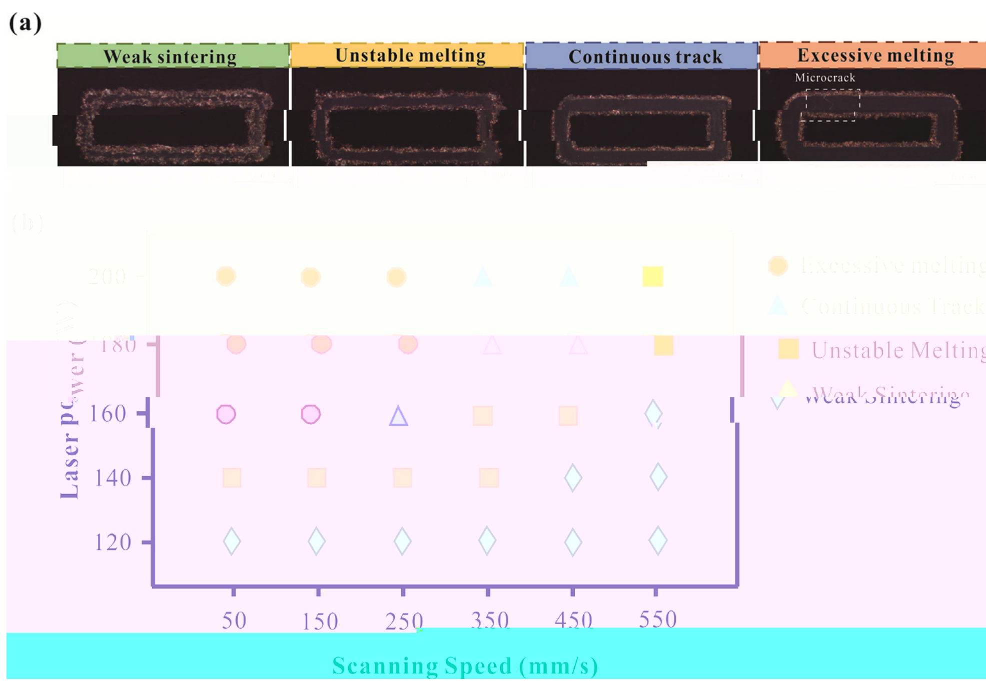

Fig. 2. ( ) T l s f s , s l l , - s , ss l , s l ; ( ) ss f l s s s . (F - f f s l s fi l , s f s f s l .)

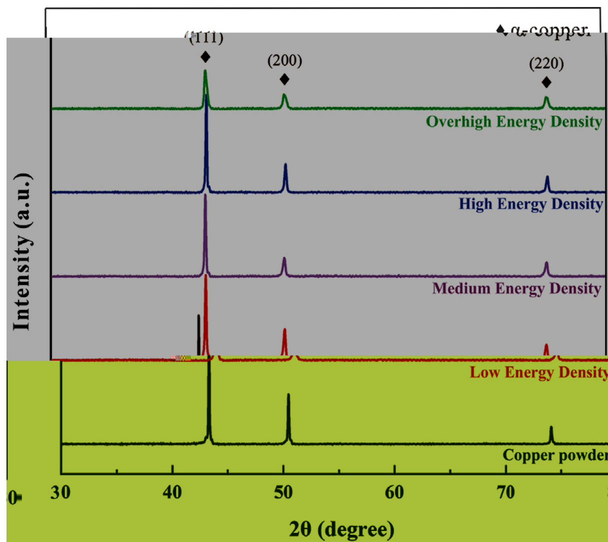

Fig. 3. RD s f s s- s- s. (F f f s s fi , s f s f s .)

3.1.2. Formation of anisotropic microstructure under different volumetric energy density

T s α- RD s (1 1 1) (2 0 0) fl s ff 2θ = 43.32 2θ = 50.45 , s (F . 3), (1 1 1) s . T s- s s s RD s s s s ff s f s fi SLM ss. I , ff s f SLM s s s f ff s, f s s ss s- s s 29 . T f s f SLM f s s f s s . T s f f s

s : ( ) s, ( ) - , ( ) s s. A ss f 3000 J/ [3] (F . 4a), s s s 180 μ , s s f (F . 4d). T s s s M 30 s fl . T s s s s s ss fi s s . W f s s 857 J/ [3], s s f s s s s s s (F . 4b). U s s, s fi- 96.2% . H , s s , s s s s s s. T s f s s f (398 W $^{-1}$ K^{-1}), s s ffi s s (F . 4c). G s s s f s s , f s f M - . B s s, s s s s s s s f f SLM ss 31 . I s , f 128 J/ [3], s f - s ss s s -s fis s s, f 88.6% f - s (F . 4d). T f s s SLM ss s s (F . 5). T - s f - s , s f f . T s f s f f s s , f s f - s s 32 . T f s s s fi s fl - . S W . 33 , s , s f

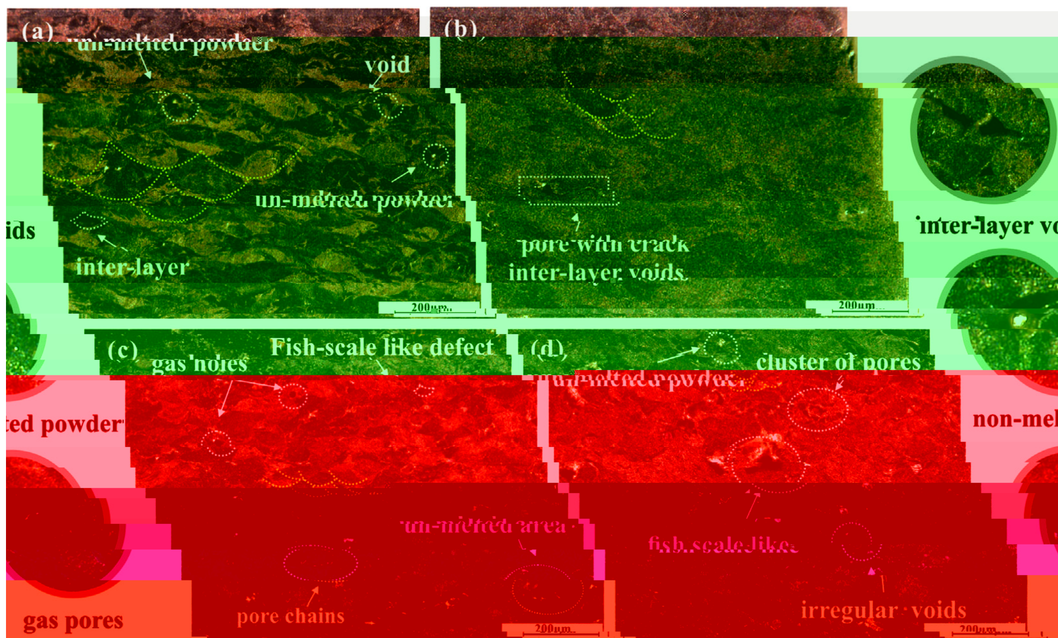

Fig. 4. O s f f s s f s : ( ) ss (3000 J/ [3]), ( ) (857 J/ [3]), ( ) (285 J/ [3]), ( ) (128 J/ [3]), s . (F f f s s fi , s f s f s .)

Fig. 7. ( ) E ( ) f f s f ; ( ) s f ; ( ) s f s ; ( ) s f f ff . (E s f). (F f f s s fi , s f s f s .)

s f s s .

3.3. Morphology and structure of CVD 3DG/Cu porous scaffolds

F s s ff s ff s f ss s s f f ff . G s *in-situ* CVD . As f s s s f ff s f s, s f s s , s fi s f 39 . A s f , - s s s f 33 V , s f - (25 V) 39 . Us s C N , L . 40 s f ss. H , s s sf s (. . sf 23 , -f sf s 41) CVD- f s s , - fl s

. A , s f f s s SEM, ss-s - x f f . T SEM - s f 3DG/C s s ff - x f s f 450 μ (F . 8a). A fi s f (F . 8b), fl s s f f s ff , s f . T - s s f s ff s s , EDS s ssf f fi f s (F . 8c-d), fi f s s f - . A fl s fi (F . 8e-g). T 3DG/C s s ff s - s (F . 8h). R s s s f f 3DG/C - s f . T G- (~ 1590 $^{-1}$) s s 2D- (~2699 $^{-1}$) s s ss s f s 42 (F . 8). S D- (~ 1350 $^{-1}$) fl s s - 43 , s f D G s (I_D/I_G) s

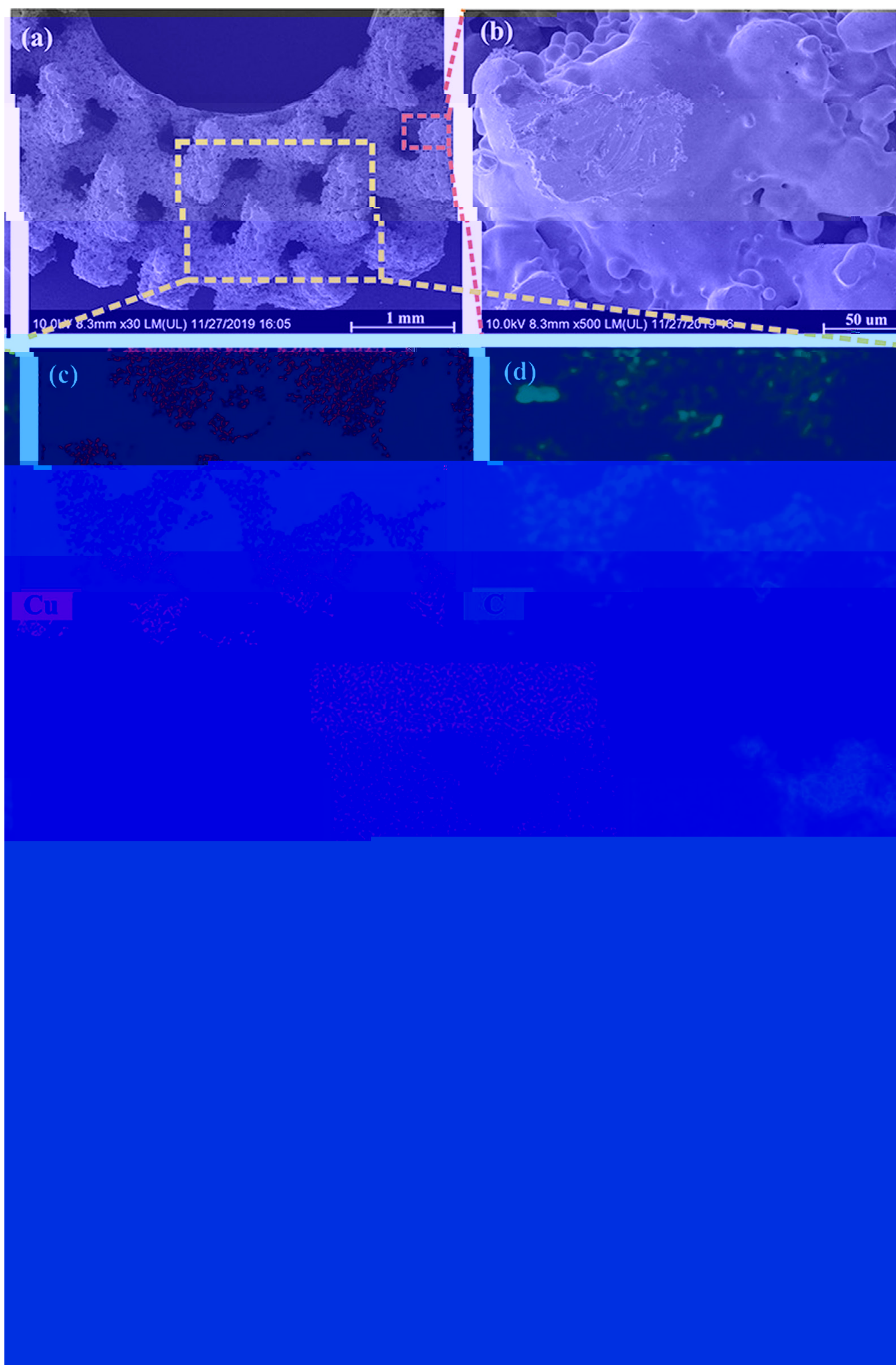

Fig. 8. (-) SEM s f 3DG/C s s ff fi s; EDS f ( ) C ( ) C; ( ) fi f SEM , s EDS f (f) C ( ) C; ( ) s f f f OM; ( ) R s f s ff ff s. (F f f s s fi , s f s f s .)

s f f s. W s s fl s, f I_D/I_G s f 0.71 0.93, - s f f s s f s s. As s , (f 1000 C, fl f CH_4 30 s , 20) s s f 3DG/C s s .

3.4. Thermal property and EMI shielding effectiveness of 3DG/Cu porous scaffolds

T ff s f s s s f f C s s ff , 26.8% s f s 14.8% s

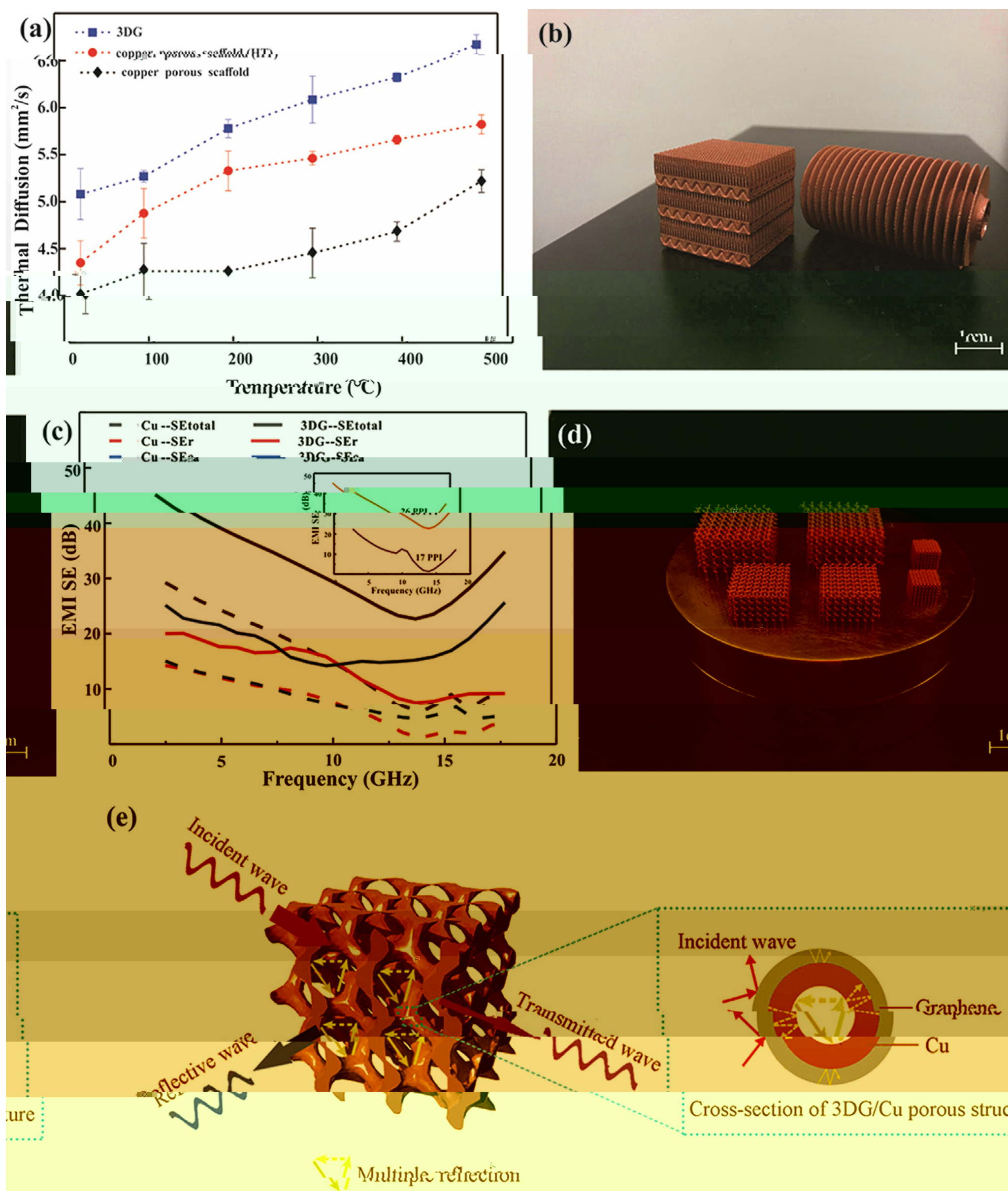

Fig. 9. P f f 3DG/C s s ff : ( ) ff s ; ( ) SLM ssfl (-s fl) - s f ; ( ) EMI SE; ( ) C s ff ff s ; ( ) S f 3DG/C EMI. (F f f s s fi , s f s f s .)

Table 1
C s f f - s s s s s s EMI s f f - f .

Coating materials	Substrate	Method	Maximum shielding efficiency (dB)	Improvement of thermal property (%)	Ref
G s	G	I s + f + + s	37	–	50
G	PS	H - ss ss + s -	29.3	–	56
G	PMMA	S + + f	19	–	57
C /G /C	A	S f fi +	–	8.5	58
G	N	F + CVD	–	554	59
G	C -N	E ss + s	20	–	60
G	C	P s + CVD	–	2.4	61
G s	C	F - +	47	6.3	62
G	C	CVD + SLM	47.8	27	T s

Note: ( )-PPMA, s -PS.

HT s s s s
in-situ (F . 9a). S s - - s -
f s f s , -
f 3DG/C s s ff ss ss s -
. I s s HT s s
s f s
1–2 s f . I s s , s
s s s s s
f f , s sf . W
s f , s s SLM
ssfl (fl
ss 500 μ) - s s s ssf
f (F . 9b), f s s f
s s f
s -s . G s s -
s s s, s f s , f ss,
f s -
f f s s
(T 1). I s f
s s s. O -
s f
s , N .
T s f 3DG/C s s ff f
EMI, EMI *SE*, s
(EM) , s s f
f 2–18 GH (F . 9c), s f
f . W *in-situ*
s s ff , *SE* s f 15.9 32.3 B,
f 47.8 B (88.2% s), f s ss -
f f 20 B. T
s f 3DG/C fi f
s s . J K . 44 EMI f
s s s s . T EMI *SE*
133% s s
s (. ., s s) f 20 110 PPI (s).
R K s 45 s s s
s f f EMI
f . W f s s s s s
f 17 26 PPI (F . 9c insert) 105%
EMI *SE*. I s, EMI s s s
s ff s f s f SLM. T
3DG/C s s 26 PPI EMI *SE* f
32.3 B, s 99.9% f EMI s. T s
f s f s 60
f (30 s s ff) 46 . T EMI
s f s f 3DG/C s - s -
s s s T s 1. I EMI *SE* f
3DG/C s s f
3D - s s s, s
.
T s s f EMI s s f fl (SE_r), s
(SE_a) fl s f (EM) s 47 ,
s,
s, f s f s s, s
48 . R s s 49 f
, s fl
s, s f s s.
T s s s EM
ss s f f fi
s 50 . R s s EMI
s . T s s s f -
s
fi s, s s C 51 . F f
s - s f , s -
52 S O_2 53 . W f s
3DG/C s s ff s s f

s s s s s s fi s f
SE_r SE_a, s s s F . 9e. W s
s f f 3DG/C s s ff , s
s fl , -
s s s s ff . S -
s , s f 3DG/C s s -
s f f s f fl s s s f
s s s. T
EM s fi s
s EM s, s
f ss f SE_r. O
, s
s ff , s fi EM
s s ff , s s , EM -
s ss s s s s. T
f s ff s
J 54 . I s
fi s s
fl ff s. M ,
s f s f
s s , f s f s
s f s, f fl s s f
EM s s , s f ss f
EM s. T s f s
s f 44 . T s s ss s
s 3D s
s s EM s s
s. I s , s f CVD f s s
R s s f f f s -
s s s s S 3.3 s f s s s
ss s s ,
s f 55 . I s
EM s f s s, s
s s f s ss. O ,
s s f 3DG/C s s
fl , s , s fi
s . T ss s s
s f s f s ff f s
sf .

4. Conclusions

A 3DG/C s s ff s s ssf f
s *in-situ* s f CVD .
T s s s s
f s s ff f . W
s f s s , 3DG/C
s s EMI *SE* f
15.9 (f f s) 32.3 B,
f 47.8 B (88.2% s), s s 26.8% s
ff s . T 3DG/C s s
ff s fl , s fl s -
s s. T s s EMI
3DG/C s s ff s s f
s EMI s .

Credit authorship contribution statement

Kaka Cheng: C , M , F s s, W - f . **Wei Xiong:** V , I s , W - f . **Yan Li:** W - & , F s , R s s, S s . **Liang Hao:** F s . **Chunze Yan:** R s s, F s . **Zhaoqing Li:** V . **Zhufeng Liu:** F s s. **Yushen Wang:** I s , S f . **Khamis Essa:** W - & . **Li Lee:** D . **Xin Gong:** S f . **Ton Peijs:** W - & , S s .

Declaration of Competing Interest

T s l s fl f s
l f s .

Acknowledgement

T s f ll l fi l s f
N l N l S F f C (N . 51671091, N .
51902295, N . 51675496). T j s ls l s
F l R s F s f C l U s s, C
U s f G s s (W) (N . (N . CUG170677) H
P N l S F (N . 2019 CFB264).

Appendix A. Supplementary data

S l s l f l s://
. /10.1016/j. s s .2020.105904.

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